

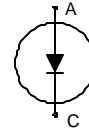
## Fast switching diode chip in Emitter Controlled -Technology

### Features:

- 1700V technology, Emitter Controlled
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

### This chip is used for:

- power modules and discrete devices



### Applications:

- SMPS, resonant applications, drives

Chip Type	$V_R$	$I_F$	Die Size	Package
SIDC73D170E6	1700V	100A	8.53 x 8.53 mm <sup>2</sup>	sawn on foil

### Mechanical Parameter

Raster size	8.53 x 8.53	mm <sup>2</sup>
Area total	72.76	
Anode pad size	6.51 x 6.51	
Thickness	200	µm
Wafer size	150	mm
Max. possible chips per wafer	189	
Passivation frontside	Photoimide	
Pad metal	3200 nm AlSiCu	
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	Electrically conductive glue or solder	
Wire bond	Al, ≤500µm	
Reject ink dot size	Ø 0.65mm; max 1.2mm	
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C	



# SIDC73D170E6

## Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} = 25\text{ °C}$	1700	V
Continuous forward current	$I_F$	$T_{vj} < 150\text{ °C}$	<sup>1)</sup>	A
Maximum repetitive forward current	$I_{FRM}$	$T_{vj} < 150\text{ °C}$	200	
Junction temperature range	$T_{vj}$		-40...+175	°C
Operating junction temperature	$T_{vj}$		-40...+150	°C
Dynamic ruggedness <sup>2)</sup>	$P_{max}$	$I_{Fmax} = 200\text{A}$ , $V_{Rmax} = 1700\text{V}$ $T_{vj} \leq 150\text{ °C}$	tbd	kW

<sup>1)</sup> depending on thermal properties of assembly

<sup>2)</sup> not subject to production test - verified by design/characterisation

## Static Characteristic (tested on wafer), $T_{vj} = 25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Reverse leakage current	$I_R$	$V_R = 1700\text{V}$			27	$\mu\text{A}$
Cathode -Anode breakdown Voltage	$V_{BR}$	$I_R = 4\text{m A}$	1700			V
Diode forward voltage	$V_F$	$I_F = 100\text{A}$		2.15		V

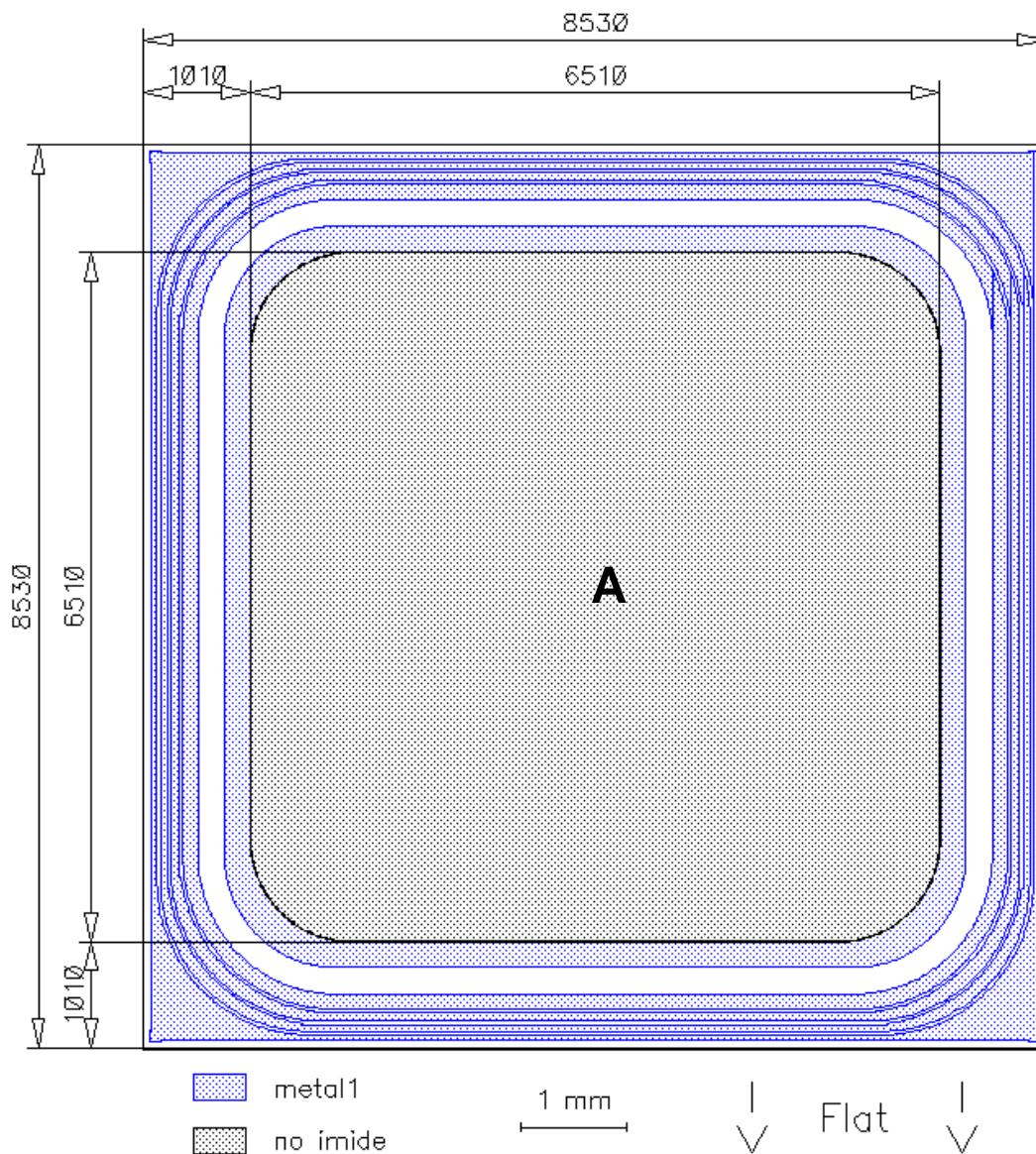
## Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

## Chip Drawing

Die-Size 8530 um x 8530 um

L4381N = I438d1



A: Anode pad



# SIDC73D170E6

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## Description

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AQL 0.65 for visual inspection according to failure catalogue

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Electrostatic Discharge Sensitive Device according to MIL-STD 883

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